

Type Designator: 2SD65

Material of Transistor: Ge

Polarity: NPN

Maximum Collector Power Dissipation (P_c): 0.12 W

Maximum Collector-Base Voltage $|V_{cb}|$: 25 V

Maximum Collector-Emitter Voltage $|V_{ce}|$: 20 V

Maximum Emitter-Base Voltage $|V_{eb}|$: 10 V

Maximum Collector Current $|I_c \text{ max}|$: 0.1 A

Max. Operating Junction Temperature (T_j): 150 °C

Transition Frequency (f_t): 0.5 MHz

Forward Current Transfer Ratio (h_{FE}), MIN: 25

Noise Figure, dB: -

Package: TO18